

Silicon PNP Power Transistors

2SB1223

DESCRIPTION

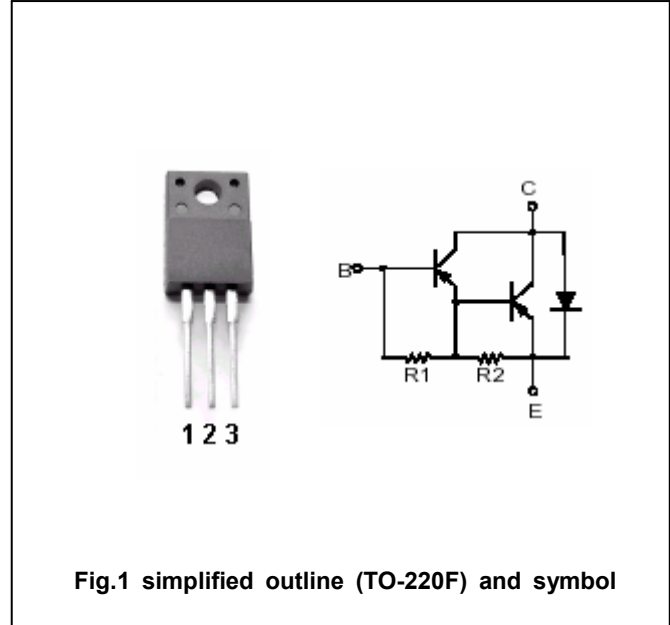
- With TO-220F package
- Complement to type 2SD1825
- High DC current gain.
- Large current capacity and wide ASO.
- DARLINGTON

APPLICATIONS

- Suitable for use in control of motor drivers, printer hammer drivers, and constant-voltage regulators.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-70	V
V _{CEO}	Collector-emitter voltage	Open base	-60	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-4	A
I _{CM}	Collector current-peak		-6	A
P _C	Collector dissipation	T _C =25℃	20	W
		T _a =25	2	
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-5mA; I _E =0	-70			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA; R _{BE} =∞	-60			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A; I _B =-4mA		-1.0	-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2A; I _B =-4mA			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-40V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-3.0	mA
h _{FE}	DC current gain	I _C =-2A; V _{CE} =-2V	2000	5000		
f _T	Transition frequency	I _C =-2A; V _{CE} =-5V		20		MHz

Switching times

t _{on}	Turn-on time	I _C =500I _{B1} =-500I _{B2} =-2A V _{CC} =-20V, R _L =10Ω		0.5		μs
t _{stg}	Storage time			1.4		μs
t _f	Fall time			1.2		μs

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PACKAGE OUTLINE

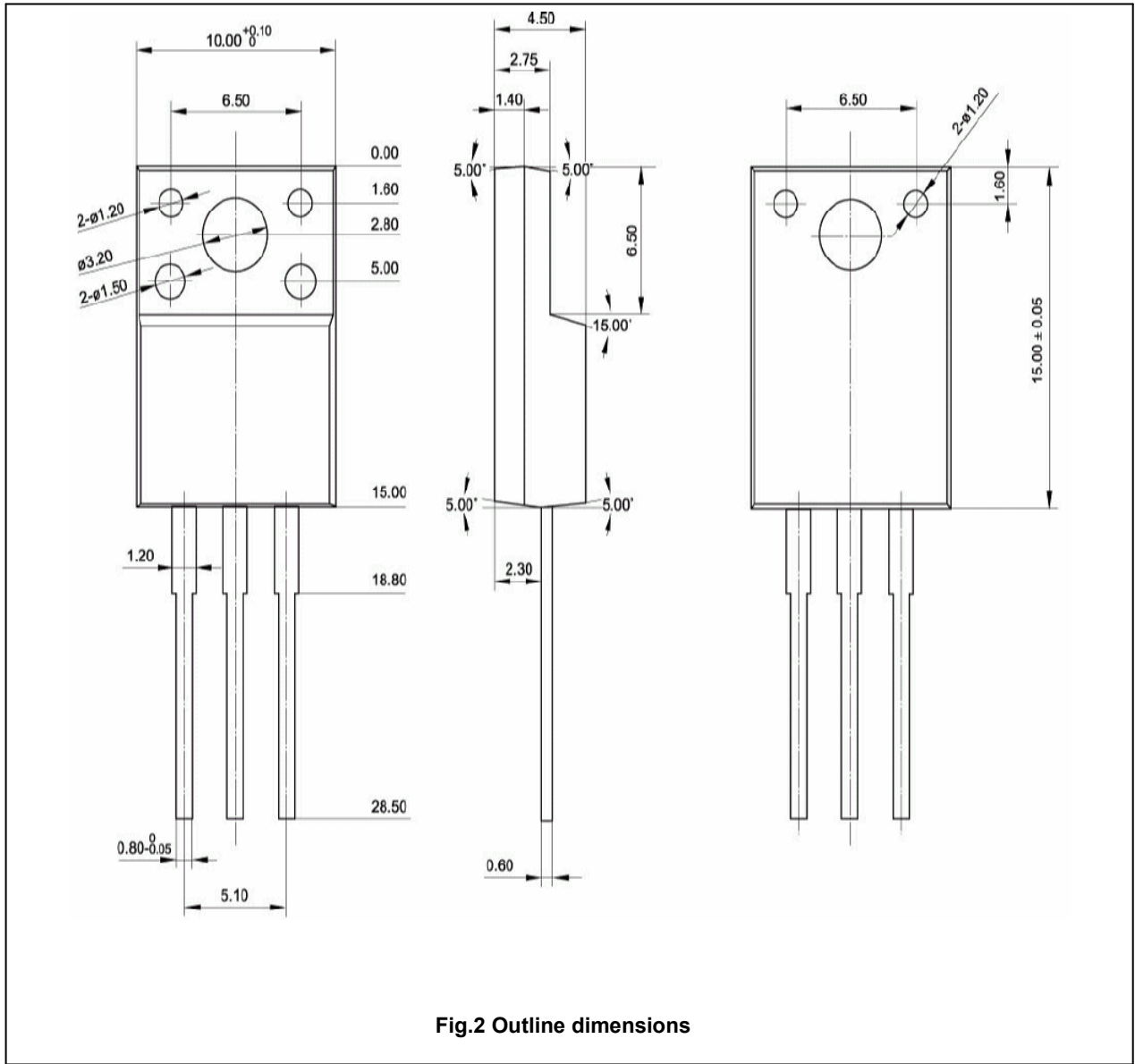


Fig.2 Outline dimensions